L Number	Hits	Search Text	DB	Time stamp
7	2	heater near4 heat adj sink adj material	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/31 10:15
8	23	heater same heat adj sink adj material	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/31 10:18
9	24	iii near2 nitride and (both adj side) same deposit$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/31 10:20
10	78	iii near2 nitride and (top same bottom) same deposit$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/31 10:25
11	96	double near2 sid$2 near2 (epitax$4 or deposit$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/31 10:27
14	4	(double near2 sid$2 near2 (epitax$4 or deposit$4)) and 117/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/31 10:37
-	2	(layer$3 same substrate same (gan or gallium adj nitride or sapphire or zinc adj oxide or zno or silicon adj carbide or silicon or si or sic) and two near2 sid$3 same deposit$4) and 117/84-109.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/23 16:00
-	15	two near2 layer$3 near3 substrate near4 (gan or gallium adj nitride or sapphire or zinc adj oxide or zno or silicon adj carbide or silicon or si or sic) and 117/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/23 16:12
-	38	multi$1layer$3 near3 substrate and 117/$4.ccls. and (remov$3 near2 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/23 16:20
-	2	two near1 sid$3 near4 deposit$4 and 117/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/23 16:49
-	66	(both or two) near1 sid$3 same deposit$4 and 117/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/30 16:16
-	10	(both or two) near1 sid$3 same deposit$4 and 117/$4.ccls. and "III-V"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/23 17:07
-	31	"III-v" same deposit$4 and (both or two) near3 (side or sided) and 117/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/23 17:15

	11	(gan or gallium adj nitride) near2 sapphire near3 (silicon or si) and 117/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/23 17:20
	43	((sapphire or "al.sub.2o.sub.3") near3 (silicon or si) near3 (substrate or wafer) and 117/$4.ccls.) and "III-V"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/30 10:11
	19	(sapphire or "al.sub.2o.sub.3") near2 buffer and 117/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/30 10:18
	23	(sapphire or "al.sub.2o.sub.3") near2 buffer near3 (silicon or si or zinc adj oxide or zno or sic or silicon adj carbide or "III-V")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/30 10:24
	9	(sapphire same "al.sub.2o.sub.3") and 117/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/30 13:24
	4	sacrific$3 near2 substrate same (sapphire or "al.sub.2o.sub.3") and 117/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/30 13:27
	31	remov$4 near2 substrate same (sapphire or "al.sub.2o.sub.3") and 117/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/30 13:51
	39	(sapphire near4 (layer$3 or multilayer$3) near2 substrate and 117/$4.ccls.) and "iii-v"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/30 13:58
	1	sapphire same (multilayer$3) near2 substrate and 117/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/30 14:00
	3	sapphire same (layered) near2 substrate and 117/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/30 14:06
	10	(sapphire or "al.sub.2o.sub.3") near2 substrate and ("iii-v") and both near2 side and 117/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/30 14:36
	3	both near2 side near10 deposit$4 and "iii-v" and 117/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/30 14:38
	30	both near2 side same (deposit$4 or grow$4) and "iii-v" and 117/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/30 14:39
	102	selectiv$4 near2 etch$3 near5 substrate and 117/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/30 15:24

23	(selectiv$4 near2 etch$3 near5 substrate and 117/$4.ccls.) and "iii-v"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/30 16:11
11	(both or two) near1 sid$3 same deposit$4 same epitax$4 and 118/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/30 16:22
14	((both or two) near1 sid$3 near3 (deposit$4 or grow$4) and 118/$4.ccls.) and (epitax$4 or single adj crystal$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/30 16:43
25	(front near2 side and back near2 side) same (deposit$4 or grow$4) and 117/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/30 16:48
67	heat adj sink adj material same radiat$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/30 18:21
1	without near4 heat adj sink adj material same radiat$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/30 18:22
7	without near4 heat adj sink adj material	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/31 10:13

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